Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

PNP complement: PBSS5330PAS

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	30	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	5	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; $δ \le$ 0.02; T_{amb} = 25 °C	-	75	100	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	Е	emitter		1—
3	С	collector	Transparent top view	2 sym021
			DFN2020D-3 (SOT1061D)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4330PAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4330PAS	E1

8. Limiting values

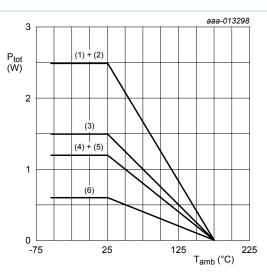
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	30	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	Α
I _B	base current			-	500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	600	mW
			[2][3]	-	1.2	W
			[4]	-	1.5	W
			[5][6]	-	2.5	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².

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- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, single-sided copper, 6 cm²
- (4) FR4 PCB, single-sided copper, 1 cm²
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uily a)	thermal resistance from junction to ambient		[1]	-	-	250	K/W
			[2][3]	-	-	125	K/W
			[4]	-	-	100	K/W
			[5][6]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Device mounted on a FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².

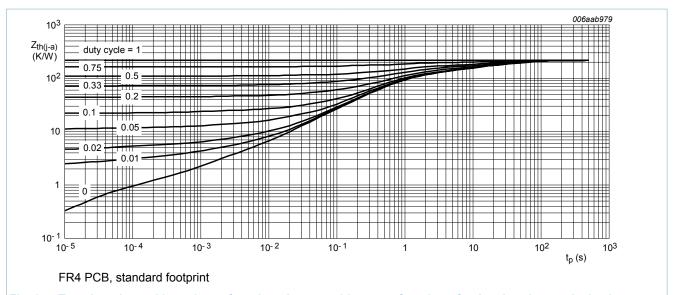


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

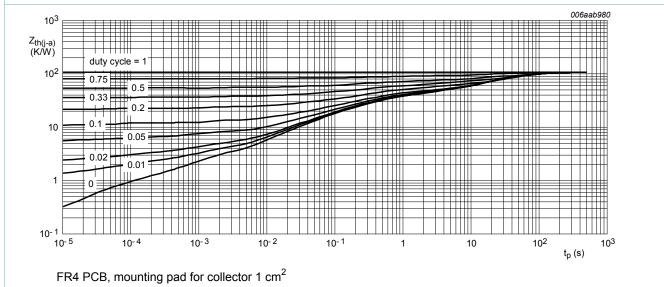


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

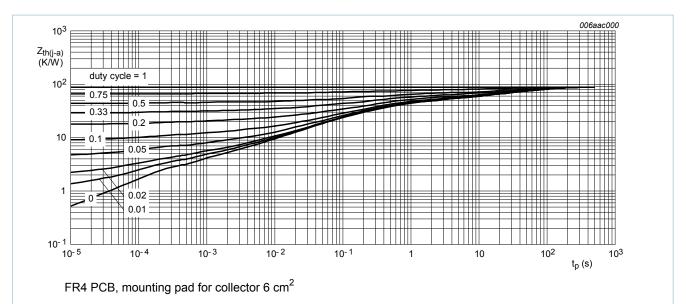


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

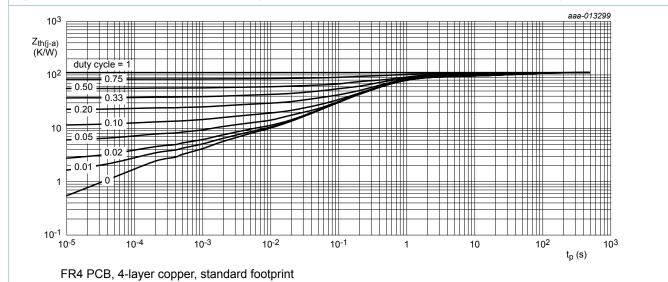


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

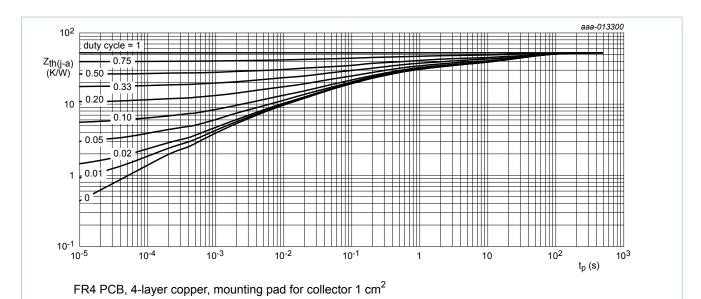


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

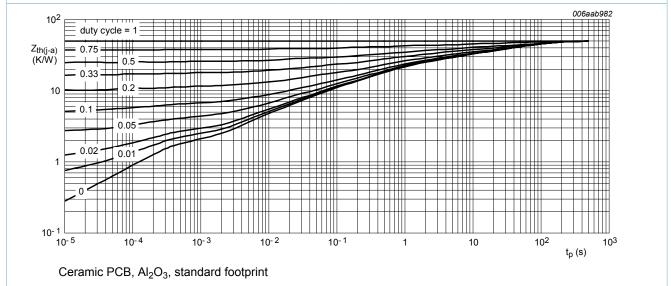


Fig. 7. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

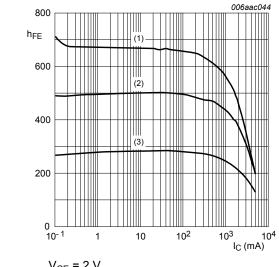
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 24 \text{ V}; I_E = 0 \text{ A}; T_j = 150 °C$	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 24 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	300	465	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	270	435	700	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	230	370	-	
	V_{CE} = 2 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	180	310	-		
OLOGI	collector-emitter saturation voltage	I_{C} = 0.5 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	40	60	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; T_{amb} = 25 °C	-	80	110	mV
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	155	220	mV
		I _C = 3 A; I _B = 300 mA; pulsed;	-	220	300	mV
R _{CEsat}	collector-emitter saturation resistance	$t_p \le 300 \text{ μs; } \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	75	100	mΩ
V_{BEsat}	base-emitter saturation voltage	I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.95	1.1	V
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	1.07	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.76	1	V
t _d	delay time	$V_{CC} = 9 \text{ V}; I_C = 2 \text{ A}; I_{Bon} = 0.1 \text{ A};$	-	11	-	ns
t _r	rise time	I_{Boff} = -0.1 A; T_{amb} = 25 °C	-	52	-	ns
t _{on}	turn-on time		-	63	-	ns
t _s	storage time		-	230	-	ns
t _f	fall time		-	40	-	ns
t _{off}	turn-off time		-	270	_	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	100	210	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	21	30	pF



 $V_{CE} = 2 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 8. DC current gain as a function of collector current; typical values

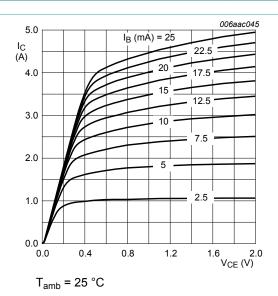
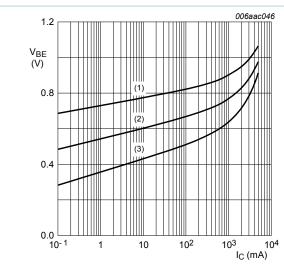


Fig. 9. Collector current as a function of collectoremitter voltage; typical values



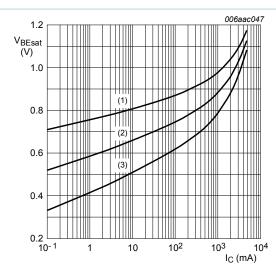
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 10. Base-emitter voltage as a function of collector current; typical values



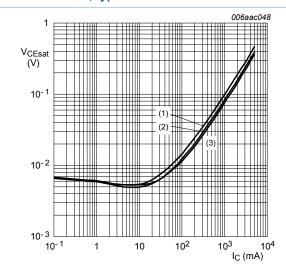
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



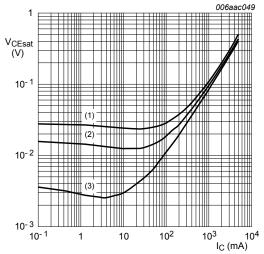
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

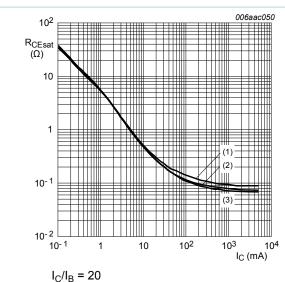


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



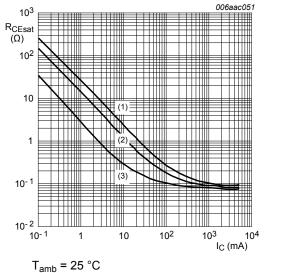
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

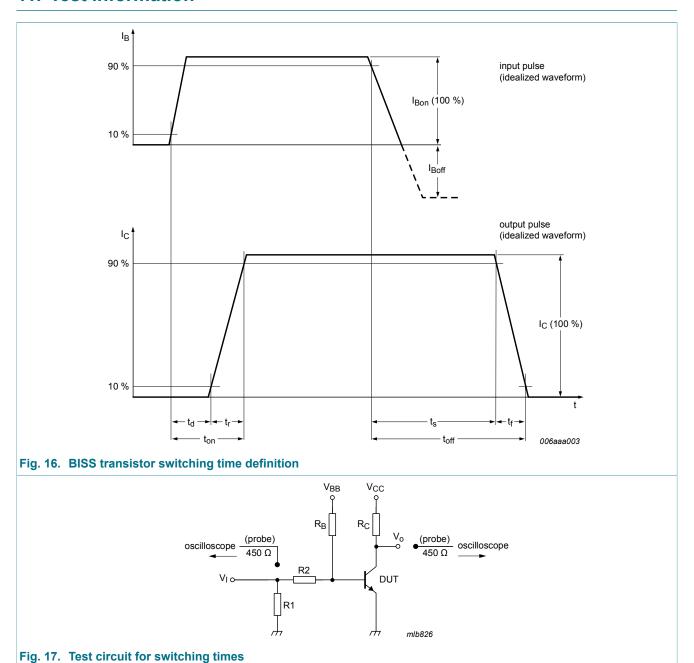
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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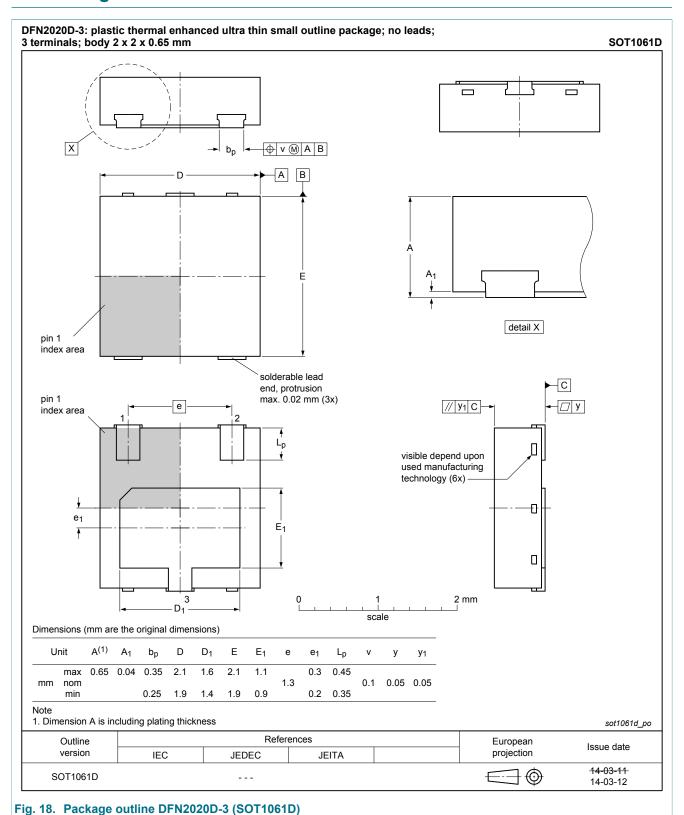
11. Test information



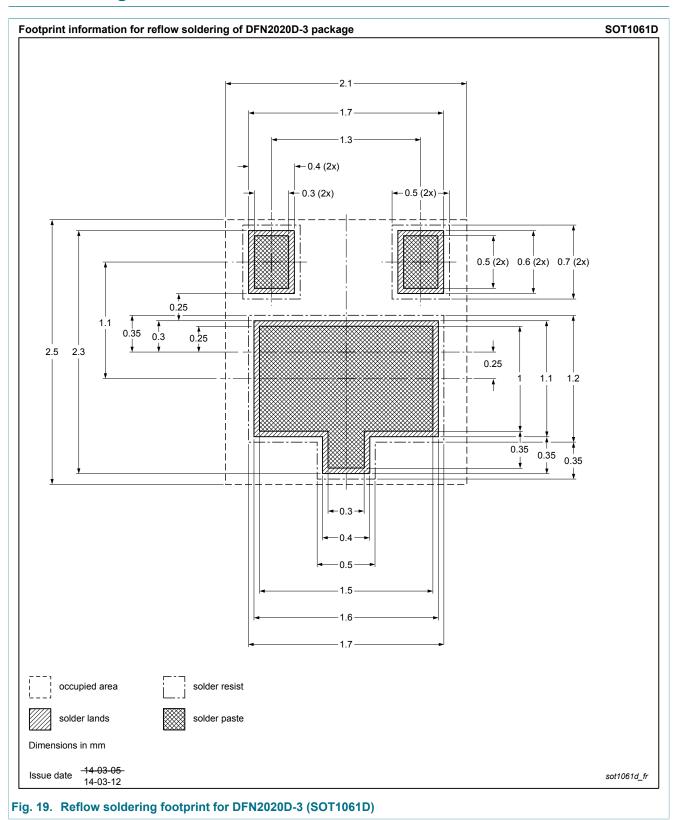
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4330PAS v.1	20140911	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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